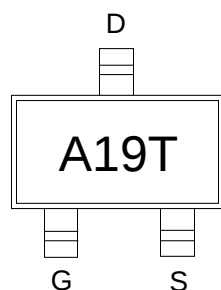


Features

- Leading trench technology for low $R_{DS(on)}$
- Low Gate Charge

Application

- Video monitor
- Power management

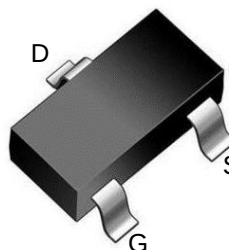


A19T: Device code

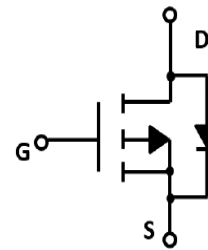
Marking and pin assignment

-20V/-2.8A P-Channel MOSFET Product Summary

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
-20V	120mΩ@4.5V	-2.8A
	150mΩ@2.5V	



SOT-23 top view

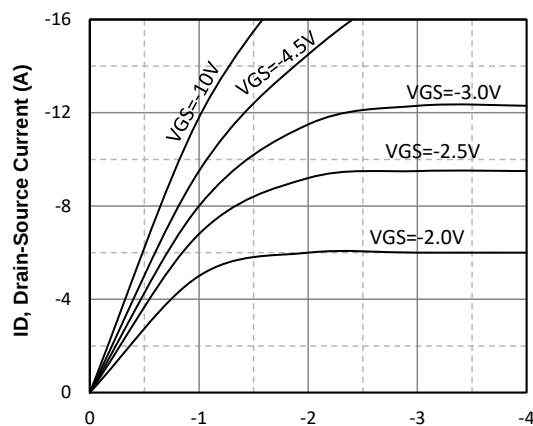


Schematic diagram

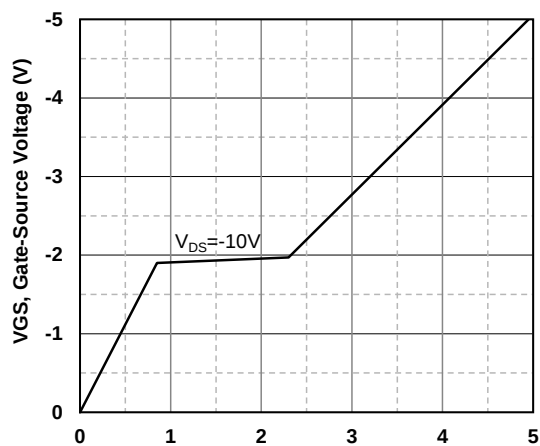
Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		-20	V
V _{GS}	Gate-Source Voltage		±10	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-2.8	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	-8.0	A
I _D	Continuous Drain Current@GS=10V	Tc=25°C	-2.8	A
P _D	Maximum Power Dissipation	Tc=25°C	0.7	W
R _{θJA}	Thermal Resistance Junction-to-Ambient		178	°C/W

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V, ID=-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	VDS=-20V, VGS=0V	--	--	-1	uA
I _{GSS}	Gate-Body Leakage Current	VGS=±10V, VDS=0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-0.4	-0.62	-1.5	V
R _{DS(on)}	Drain-Source On-State Resistance	VGS=-4.5V, ID=-2.8A	--	80	120	mΩ
		VGS=-2.5V, ID=-1.5A	--	105	150	
		VGS=-1.8V, ID=-1.5A	--	150	250	
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	VDS=-10V, VGS=0V, f=1MHz	--	327	--	pF
C _{OSS}	Output Capacitance		--	60	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	55	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	VDS=-10V, ID=-2A, VGS=-4.5V	--	3.8	--	nC
Q _{gs}	Gate Source Charge		--	0.7	--	nC
Q _{gd}	Gate Drain Charge		--	0.9	--	nC
t _{d(on)}	Turn-on Delay Time	VDD=-10V, ID=-1A, VGS=-4.5V, RG=2.8Ω	--	6	--	nS
t _r	Turn-on Rise Time		--	31	--	nS
t _{d(off)}	Turn-Off Delay Time		--	45	--	nS
t _f	Turn-Off Fall Time		--	40	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25℃, Is=-2.5A,	--	--	-1.2	V

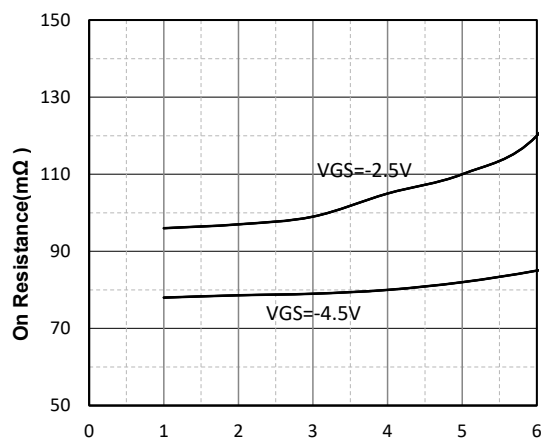
Typical Operating Characteristics



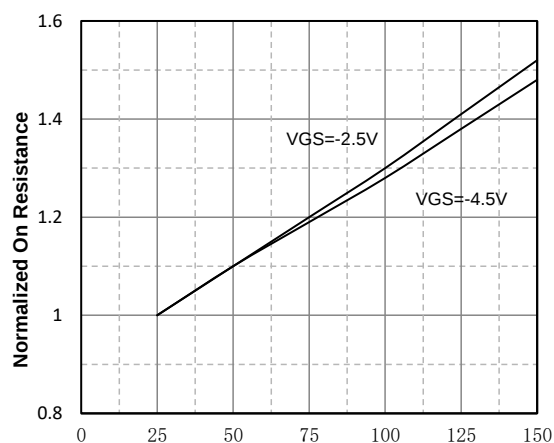
VDS, Drain -Source Voltage (V)
Fig1. Typical Output Characteristics



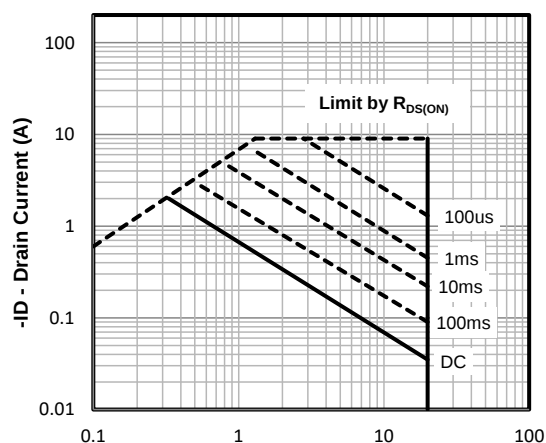
Qg -Total Gate Charge (nC)
Fig2. Typical Gate Charge Vs. Gate-Source Voltage



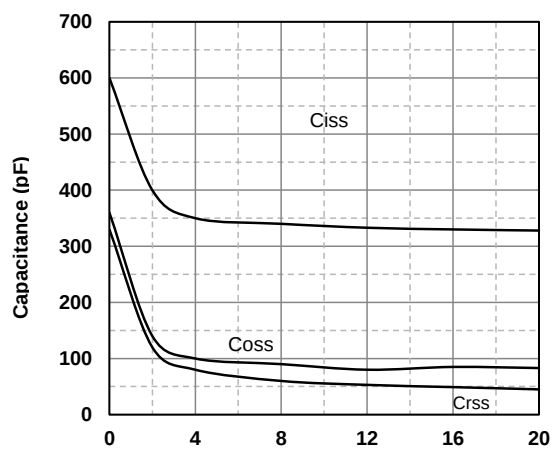
ID, Drain-Source Current (mA)
Fig3. Drain-Source on Resistance



Tj - Junction Temperature (°C)
Fig4. Normalized On-Resistance Vs. Temperature

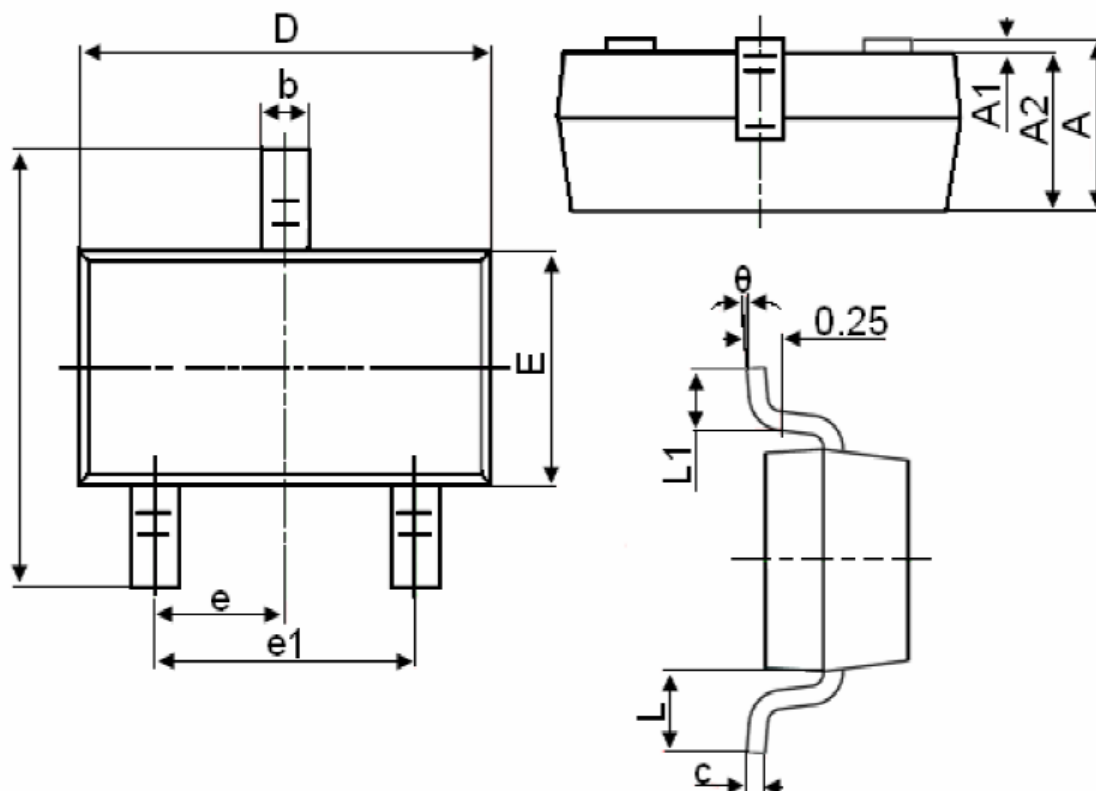


-VDS, Drain -Source Voltage (V)
Fig5. Maximum Safe Operating Area



-VDS, Drain-Source Voltage (V)
Fig6. Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°